CLAIMS

[Claim 1]

A composition comprising saccharin and water, and the pH being no greater than 9.7, when used to remove photoresist residue and/or polymer residue after dry etching or wet etching using a photoresist as a mask.

[Claim 2]

The composition according to Claim 1, wherein it further comprises one or more types of substance selected from the group consisting of (A) a water-soluble solvent, (B) an acid, and (C) a dissociable nitrogen-containing compound.

[Claim 3]

The composition according to Claim 1 or 2, wherein the content of saccharin is at least 0.01 mass%.

[Claim 4]

Use of a composition comprising saccharin and water, and the pH being no greater than 9.7, for removing photoresist residue and/or polymer residue after dry etching or wet etching using a photoresist as a mask.

[Claim 5]

The use according to Claim 4, wherein the composition further comprises one or more types of substance selected from the group consisting of (A) a water-soluble solvent, (B) an acid, and (C) a dissociable nitrogen-containing compound.

[Claim 6]

The use according to Claim 4 or 5, wherein the content of saccharin comprised in the composition is at least 0.01 mass%.

[Claim 7]

A method for removing photoresist residue and/or polymer residue, the method comprising the following step:

using a composition comprising saccharin and water, and the pH being no greater than 9.7, to remove photoresist residue and/or polymer residue on a substrate after dry etching or wet etching using a photoresist as a mask.

[Claim 8]

The method according to Claim 7, wherein the composition further comprises one or more types of substance selected from the group consisting of (A) a water-soluble solvent, (B) an acid, and (C) a dissociable nitrogen-containing compound.

[Claim 9]

The method according to Claim 7 or 8, wherein the content of saccharin comprised in the composition is at least 0.01 mass%.